Abstracts

Millimeter-Wave HEMT Noise Models Verified Thru V-Band

M.D. DuFault and A.K. Sharma. "Millimeter-Wave HEMT Noise Models Verified Thru V-Band." 1996 MTT-S International Microwave Symposium Digest 96.3 (1996 Vol. III [MWSYM]): 1321-1324.

Further enhancements in the HEMT noise modeling procedure described in [1] now enables scaling of bias dependent noise models, This was experimentally verified through V-band using prematched structures utilizing the TRW 0.1µm gate length low noise process. With this procedure, it is now possible to scale device noise models obtained at microwave frequencies to millimeter wave frequencies with good correlation. The scaled models are further verified with Q- and V-band low noise amplifiers.

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